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July 2014

FDMA1025P

Dual P-Channel PowerTrench® MOSFET

-20V, -3.1A, 155mΩ

Features

- Max $r_{DS(on)}$ = 155m Ω at V_{GS} = -4.5V, I_D = -3.1A
- Max $r_{DS(on)} = 220 m\Omega$ at $V_{GS} = -2.5 V$, $I_D = -2.3 A$
- Low profile 0.8mm maximum in the new package MicroFET 2X2 mm
- RoHS Compliant
- Free from halogenated compounds and antimony



General Description

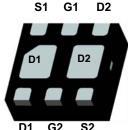
This device is designed specifically as a single package solution for the battery charge switch in cellular handset and other ultraportable applications. It features two independent P-Channel MOSFETs with low on-state resistance for minimum conduction losses. When connected in the typical common source configuration, bi-directional current flow is possible.

The MicroFET 2X2 package offers exceptional thermal performance for its physical size and well suited to linear mode applications.

Application

■ DC - DC Conversion





PIN 1

S1 1 6 D1
G1 2 5 G2
D2 3 4 S2

MicroFET 2X2

MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DS}	Drain to Source Voltage		-20	V
V_{GS}	Gate to Source Voltage		±12	V
	Drain Current -Continuous	(Note 1a)	-3.1	Α
^I D	-Pulsed		-6	7 ^
D	Power Dissipation for Single Operation	(Note 1a)	1.4	W
P_{D}	Power Dissipation	(Note 1b)	0.7] vv
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance Single Operation, Junction to Ambient	(Note 1a)	86	
$R_{\theta JA}$	Thermal Resistance Single Operation, Junction to Ambient	(Note 1b)	173	°C/W
$R_{\theta JA}$	Thermal Resistance Dual Operation, Junction to Ambient	(Note 1c)	69	C/VV
$R_{\theta JA}$	Thermal Resistance Dual Operation, Junction to Ambient	(Note 1d)	151	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
025	FDMA1025P	MicroFET 2X2	7"	8mm	3000 units

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test (Conditions	Min	Тур	Max	Units
Off Chara	acteristics						
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_C$	_{SS} = 0V	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I _D = -250μA, ref	erenced to 25°C		14		mV/°C
	7 0 1 1/1 5 1 0 1	V _{DS} = -16V,				-1	
IDSS	Zero Gate Voltage Drain Current	V _{GS} = 0V	T _J = 125°C			-100	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 12V, V_{D}$	S = 0V			±100	nA

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250 \mu A$	-0.4	-0.9	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I _D = -250μA, referenced to 25°C		-3.8		mV/°C
		$V_{GS} = -4.5V, I_D = -3.1A$		88	155	
r _{DS(on)}	Drain to Source On Resistance	$V_{GS} = -2.5V, I_D = -2.3A$		144	220	mΩ
	$V_{GS} = -4.5V$, $I_D = -3.1A$, $T_J = 125$ °C		121	220		
9 _{FS}	Forward Transconductance	$V_{DS} = -5V, I_D = -3.1A$		6.2		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 40V V - 0V	340	450	pF
C _{oss}	Output Capacitance	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1MHz	80	105	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1101112	45	70	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		5	10	ns
t _r	Rise Time	$V_{DD} = -10V$, $I_{D} = -3.1A$ $V_{GS} = -4.5V$, $R_{GEN} = 6\Omega$	14	26	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = -4.5V, R_{GEN} = 612$	13	24	ns
t _f	Fall Time		8	16	ns
Q _{g(TOT)}	Total Gate Charge at 4.5V	$V_{GS} = 0V \text{ to } -4.5V$ $V_{DD} = -10V$	3.4	4.8	nC
Q _{gs}	Gate to Source Gate Charge	$I_{D} = -3.1A$	0.8		nC
Q _{gd}	Gate to Drain "Miller" Charge		1.0		nC

Drain-Source Diode Characteristics

I _S	Maximum Continuous Source-Drain Diode Forward				-1.1	Α
V_{SD}	Source to Drain Diode Forward Voltage V _{GS} = 0V, I _S = -1.1A (Note 2)			-0.8	-1.2	V
t _{rr}	Reverse Recovery Time	ไ⊑ = –3.1A. di/dt = 100A/นร		17	26	ns
Q _{rr}	Reverse Recovery Charge	1F = -3.1A, di/dt = 100A/μs		10	15	nC

- 1. $R_{\theta JA}$ is determined with the device mounted on a 1 in 2 oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.

 (a) $R_{0JA} = 86$ °C/W when mounted on a 1 in² pad of 2 oz copper, 1.5 " x 1.5 " x 0.062 " thick PCB. For single operation.

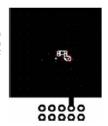
 - (b) $\rm R_{\theta JA}$ = 173 °C/W when mounted on a minimum pad of 2 oz copper. For single operation.
 - (c) $R_{\theta JA} = 69$ °C/W when mounted on a 1 in² pad of 2 oz copper, 1.5 " x 1.5 " x 0.062 " thick PCB. For dual operation.
 - (d) $R_{\theta JA}$ = 151 °C/W when mounted on a minimum pad of 2 oz copper. For dual operation.



a)86 °C/W when mounted on a 1 in² pad of 2 oz copper.



b)173 °C/W when mounted on a minimum pad of 2 oz copper.



c)69 °C/W when mounted on a 1 in² pad of 2 oz copper.



d)151 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test : Pulse Width < 300 us, Duty Cycle < 2.0

Typical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

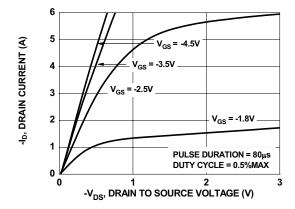


Figure 1. On Region Characteristics

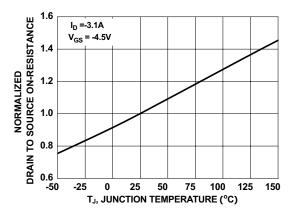


Figure 3. Normalized On Resistance vs Junction Temperature

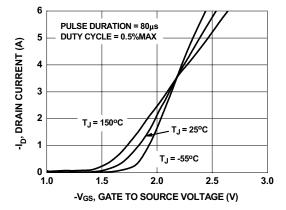


Figure 5. Transfer Characteristics

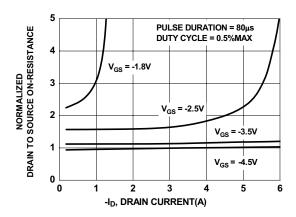


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

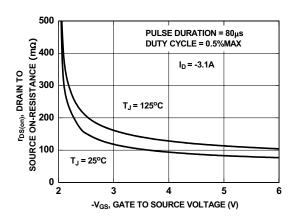


Figure 4. On-Resistance vs Gate to Source Voltage

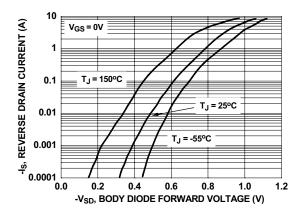


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

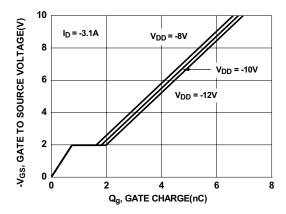


Figure 7. Gate Charge Characteristics

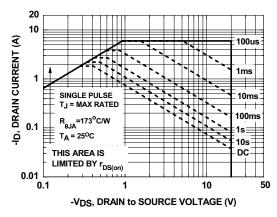


Figure 9. Forward Bias Safe Operating Area

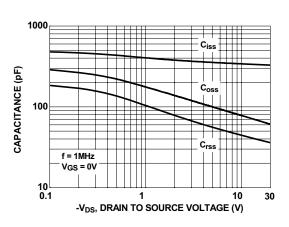


Figure 8. Capacitance vs Drain to Source Voltage

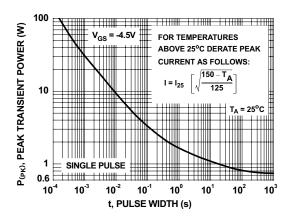
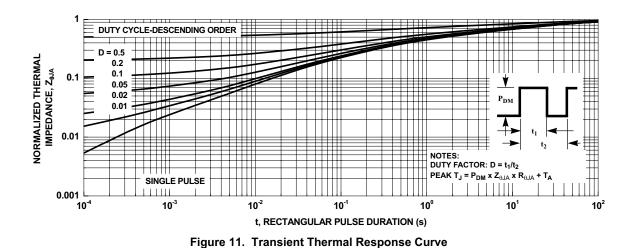
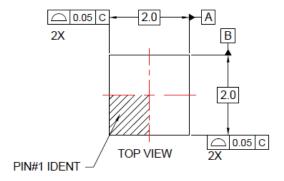
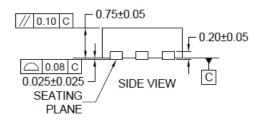


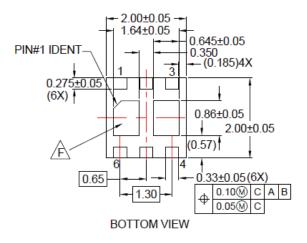
Figure 10. Single Pulse Maximum Power Dissipation

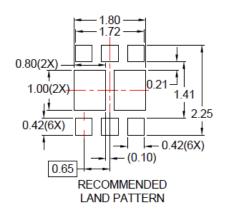


Dimensional Outline and Pad Layout









NOTES:

- A. CONFORM TO JADEC REGISTRATIONS MO-229, VARIATION VCCC, EXCEPT WHERE NOTED.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
- E. DRAWING FILENAME: MKT-UMLP16Erev4
- F. NON-JEDEC DUAL DAP



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